

10A Avg.

60 Volts

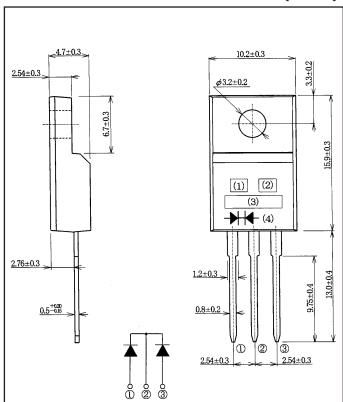
SBD

FCQ10U06

## ■最大定格 Maximum Ratings

Item	Symbol	Conditions			Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	60			V
非くり返しピーク逆電圧 Non-repetitive Peak Reverse Voltage	V <sub>RSM</sub>	65			V
平均整流電流 Average Rectified Forward Current	I <sub>O</sub>	50Hz, 正弦全波抵抗負荷 50Hz Full Sine Wave Resistive Load	T <sub>c</sub> =108°C	10	A
実効順電流 R.M.S. Forward Current	I <sub>F(RMS)</sub>	11.1			A
サージ順電流 Surge Forward Current	I <sub>FSM</sub>	110 50Hz正弦全波, 1サイクル, 非くり返し 50Hz Full Sine Wave, 1cycle, Non-repetitive			A
動作接合温度範囲 Operating Junction Temperature Range	T <sub>jw</sub>	-40~+150			°C
保存温度範囲 Storage Temperature Range	T <sub>stg</sub>	-40~+150			°C
締付トルク Mounting torque	F <sub>tor</sub>	推奨値 Recommended Value	0.5	N·m	

## ■OUTLINE DRAWING(mm)



■APPROX. NET WEIGHT:2.20 g

## ■電気的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
ピーカー逆電流 Peak Reverse Current	I <sub>RM</sub>	T <sub>j</sub> =25°C, V <sub>RRM</sub> =V <sub>RRM</sub> , 一素子あたり Per Diode	—	—	5	mA
ピーカー順電圧 Peak Forward Voltage	V <sub>FM</sub>	T <sub>j</sub> =25°C, I <sub>FM</sub> =5A, 一素子あたり Per Diode	—	—	0.58	V
熱抵抗 Thermal Resistance	R <sub>th(j-c)</sub>	接合部・ケース間 Junction to Case	—	—	3	°C/W
	R <sub>th(c-f)</sub>	ケース・フィン間 Case to Fin	—	—	1.5	°C/W

## ■定格・特性曲線

FIG.1

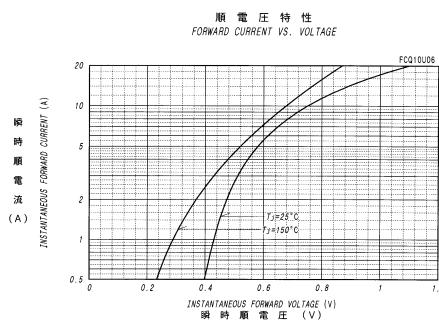


FIG.2

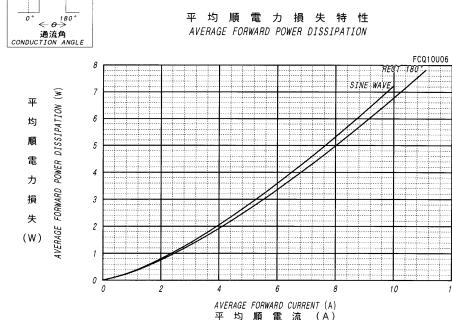


FIG.3

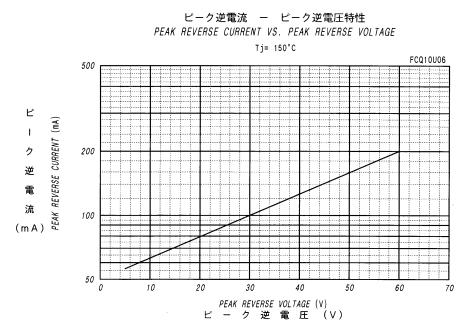


FIG.4

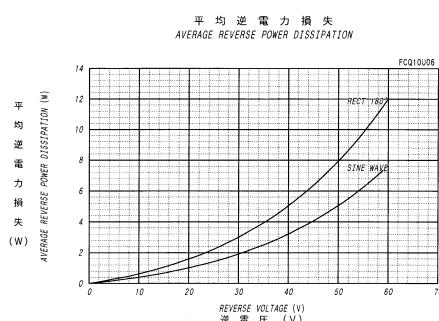


FIG.5

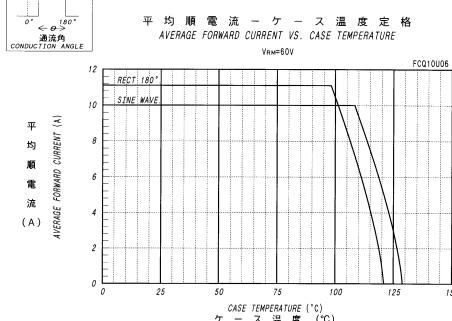


FIG.6

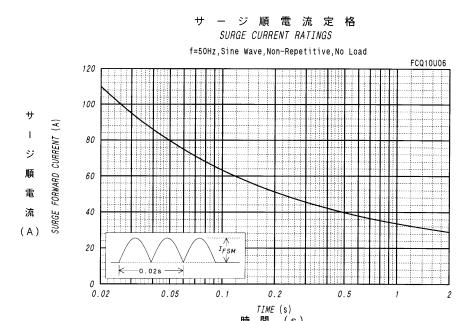


FIG.7

